

# BGA231L7

Silicon Germanium GPS Low Noise Amplifier

## Data Sheet

Revision 3.0, 2011-04-20

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**Revision History**

Page or Item	Subjects (major changes since previous revision)
<b>Revision 3.0, 2011-04-20</b>	
all	“Preliminary” status removed
<b>Revision 2.0, 2011-01-18</b>	
all	Preliminary data sheet
10, 11	Electrical Characteristics specified for frequency range $f = 1550 - 1615$ MHz
7	Marking code defined: BD

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Last Trademarks Update 2011-02-24

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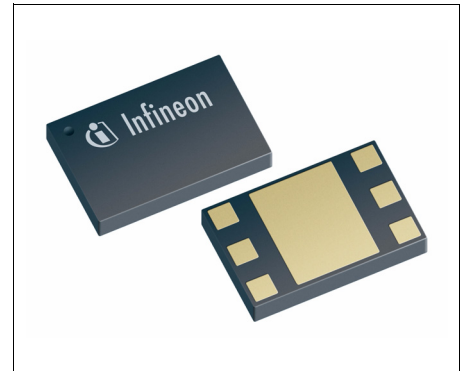
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## Features

- Insertion power gain: 16.0 dB
- High out of band input 3rd order intercept point: +5 dBm
- High input 1 dB compression point: -5 dBm
- Low Noise Figure: 0.75 dB
- Low current consumption: 4.4 mA
- Operating frequency: 1550 - 1615 MHz
- Supply voltage: 1.5 V to 3.6 V
- Digital on/off switch (1V logic high level)
- Tiny TSLP-7-1 leadless package
- B7HF Silicon Germanium technology
- RF output internally matched to 50  $\Omega$
- Only 3 external SMD components necessary
- 2 kV HBM ESD protection (including AI-pin)
- Pb-free (RoHS compliant) package



## Application

- Suitable for all Global Navigation Satellite Systems (GNSS) like GPS, Galileo, GLONASS, COMPASS

## Description

The BGA231L7 is a front-end low noise amplifier for Global Navigation Satellite Systems (GNSS) from 1550 MHz to 1615 MHz like GPS, Galileo, GLONASS and COMPASS. The LNA provides 16.0 dB gain and 0.75 dB noise figure at a current consumption of 4.4 mA in the application configuration described in [Chapter 3](#). The BGA231L7 is based upon Infineon Technologies' B7HF Silicon Germanium technology. It operates from 1.5 V to 3.6 V supply voltage.

Product Name	Marking	Package
BGA231L7	BD	TSLP-7-1

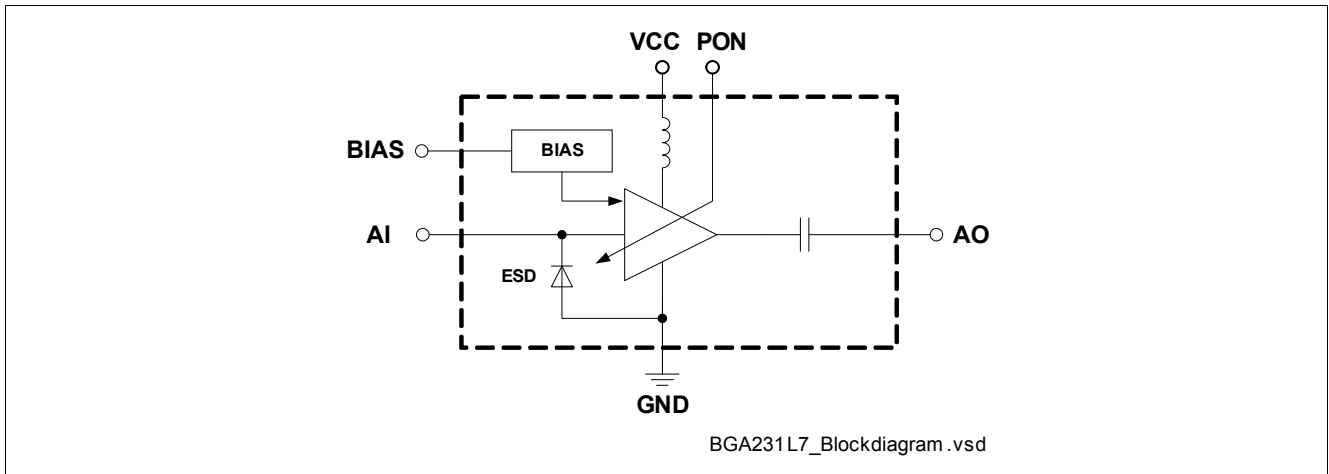


Figure 1 Block Diagram

Table 1 Pin Definition and Function

Pin No.	Name	Function
1	PON	Power on control
2	AI	LNA input
3	BIAS	DC bias
4	n.c.	not connected
5	AO	LNA output
6	VCC	DC Supply
7	GND	RF and DC ground



## 1 Maximum Ratings

**Table 2 Maximum Ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Voltage at pin VCC	$V_{CC}$	-0.3	–	3.6	V	1)
Voltage at pin AI	$V_{AI}$	-0.3	–	0.9	V	–
Voltage at pin BIAS	$V_{BIAS}$	-0.3	–	0.9	V	–
Voltage at pin AO	$V_{AO}$	-0.3	–	$V_{CC} + 0.3$	V	–
Voltage at pin PON	$V_{PON}$	-0.3	–	$V_{CC} + 0.3$	V	–
Voltage at pin VSS	$V_{SS}$	-0.3	–	0.3	V	–
Current into pin VCC	$I_{CC}$	–	–	20	mA	–
RF input power	$P_{IN}$	–	–	0	dBm	–
Total power dissipation, $T_S < 129\text{ °C}^2$ )	$T_J$	–	–	72	mW	–
Junction temperature	$P_{tot}$	–	–	150	°C	–
Ambient temperature range	$T_A$	-40	–	85	°C	–
Storage temperature range	$T_{STG}$	-65	–	150	°C	–
ESD capability all pins	$V_{ESD\_HBM}$	–	–	2000	V	according to JESD22A-114

1) All voltages refer to VSS-Node unless otherwise noted

2)  $T_S$  is measured on the ground lead at the soldering point

**Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.**

### Thermal Resistance

**Table 3 Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	291	K/W

1) For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

## 2 Electrical Characteristics

**Table 4** Electrical Characteristics:<sup>1)</sup>  $T_A = 25\text{ °C}$ ,  $V_{CC} = 2.8\text{ V}$ ,  $V_{PON,ON} = 2.8\text{ V}$ ,  $V_{PON,OFF} = 0\text{ V}$ ,  
 $f = 1550 - 1615\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	$V_{CC}$	1.5	–	3.6	V	–
Supply current	$I_{CC}$	–	4.4	–	mA	ON-mode
		–	0.2	3	$\mu\text{A}$	OFF-mode
Power On voltage	$V_{pon}$	1.0	–	$V_{CC}$	V	ON-mode
		0	–	0.4	V	OFF-mode
Power On current	$I_{pon}$	–	5	–	$\mu\text{A}$	ON-mode
		–	–	1	$\mu\text{A}$	OFF-mode
Insertion power gain	$ S_{21} ^2$	–	16.0	–	dB	
Noise figure <sup>2)</sup>	$NF$	–	0.75	1.3	dB	$Z_S = 50\ \Omega$
Input return loss	$RL_{in}$	–	10	–	dB	
Output return loss	$RL_{out}$	–	16	–	dB	
Reverse isolation	$1/ S_{12} ^2$	–	23	–	dB	
Power gain settling time <sup>3)</sup>	$t_S$	–	5	–	$\mu\text{s}$	OFF- to ON-mode
		–	5	–	$\mu\text{s}$	ON- to OFF-mode
Inband input 1 dB compression point	$IP_{1dB}$	–	-5	–	dBm	
Inband input 3rd order intercept point <sup>4)</sup>	$IIP_3$	–	0	–	dBm	$f_1 = 1575\text{ MHz}$ $f_2 = f_1 \pm 1\text{ MHz}$
Out of band input 3rd order intercept point <sup>5)</sup>	$IIP_{3oob}$	–	+5	–	dBm	$f_1 = 1712.7\text{ MHz}$ $f_2 = 1850\text{ MHz}$
Stability	$k$	–	> 1	–		$f = 20\text{ MHz} \dots 10\text{ GHz}$

1) Based on the application described in chapter 3

2) PCB losses are subtracted

3) To be within 1 dB of the final gain OFF- to ON-mode; to be within 3 dB of the final gain ON- to OFF-mode

4) Input Power = -30 dBm for each tone

5) Input Power = -20 dBm for each tone

## Electrical Characteristics

**Table 5** Electrical Characteristics:<sup>1)</sup>  $T_A = 25\text{ °C}$ ,  $V_{CC} = 1.8\text{ V}$ ,  $V_{PON,ON} = 1.8\text{ V}$ ,  $V_{PON,OFF} = 0\text{ V}$ ,  
 $f = 1550 - 1615\text{ MHz}$ 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	$V_{CC}$	1.5	–	3.6	V	–
Supply current	$I_{CC}$	–	4.4	–	mA	ON-mode
		–	0.2	3	$\mu\text{A}$	OFF-mode
Gain switch control voltage	$V_{pon}$	1.0	–	$V_{CC}$	V	ON-mode
		0	–	0.4	V	OFF-mode
Gain switch control current	$I_{pon}$	–	5	–	$\mu\text{A}$	ON-mode
		–	–	1	$\mu\text{A}$	OFF-mode
Insertion power gain	$ S_{21} ^2$	–	16.0	–	dB	
Noise figure <sup>2)</sup>	$NF$	–	0.75	1.3	dB	$Z_S = 50\ \Omega$
Input return loss	$RL_{in}$	–	10	–	dB	
Output return loss	$RL_{out}$	–	16	–	dB	
Reverse isolation	$1/ S_{12} ^2$	–	23	–	dB	
Power gain settling time <sup>3)</sup>	$t_S$	–	5	–	$\mu\text{s}$	OFF- to ON-mode
		–	5	–	$\mu\text{s}$	ON- to OFF-mode
Inband input 1 dB compression point	$IP_{1dB}$	–	-8	–	dBm	
Inband input 3rd order intercept point <sup>4)</sup>	$IIP_3$	–	0	–	dBm	$f_1 = 1575\text{ MHz}$ $f_2 = f_1 \pm 1\text{ MHz}$
Out of band input 3rd order intercept point <sup>5)</sup>	$IIP_{3oob}$	–	+5	–	dBm	$f_1 = 1712.7\text{ MHz}$ $f_2 = 1850\text{ MHz}$
Stability	$k$	–	> 1	–		$f = 20\text{ MHz} \dots 10\text{ GHz}$

1) Based on the application described in chapter 3

2) PCB losses are subtracted

3) To be within 1 dB of the final gain OFF- to ON-mode; to be within 3 dB of the final gain ON- to OFF-mode

4) Input Power = -30 dBm for each tone

5) Input Power = -20 dBm for each tone

### 3 Application Information

#### Application Board Configuration

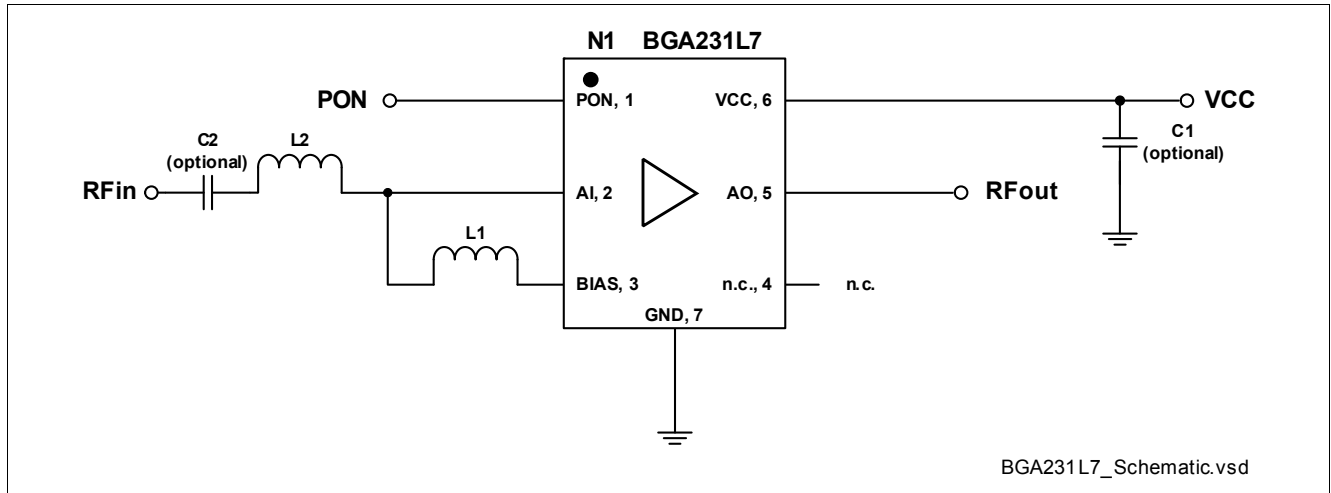


Figure 2 Application Schematic BGA231L7

Table 6 Bill of Materials

Name	Value	Package	Manufacturer	Function
C1 (optional)	100 nF	0201	Various	RF block
C2 (optional)	33 pF	0201	Various	DC block
L1	39 nH	0201	Murata LQP03T	Bias feed and RF choke
L2	6.8 nH	0201	Murata LQP03T	Input matching
N1	BGA231L7	TSLP-7-1	Infineon	SiGe LNA

A list of all application notes is available at <http://www.infineon.com/gpslna.appnotes>.

## 4 Package Information

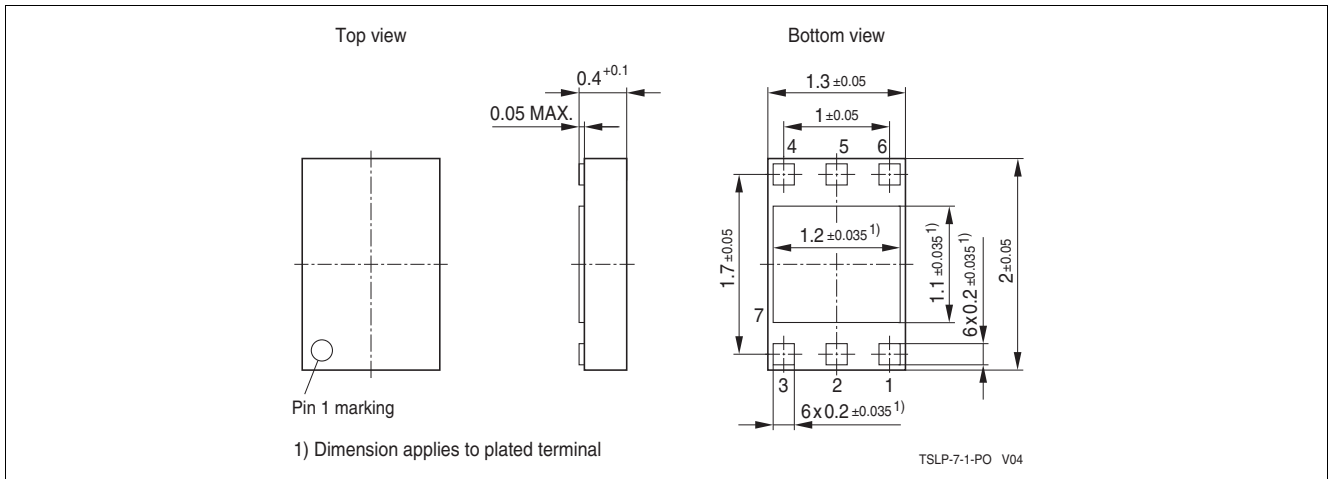


Figure 3 Package Outline TSLP-7-1 (side and bottom view)

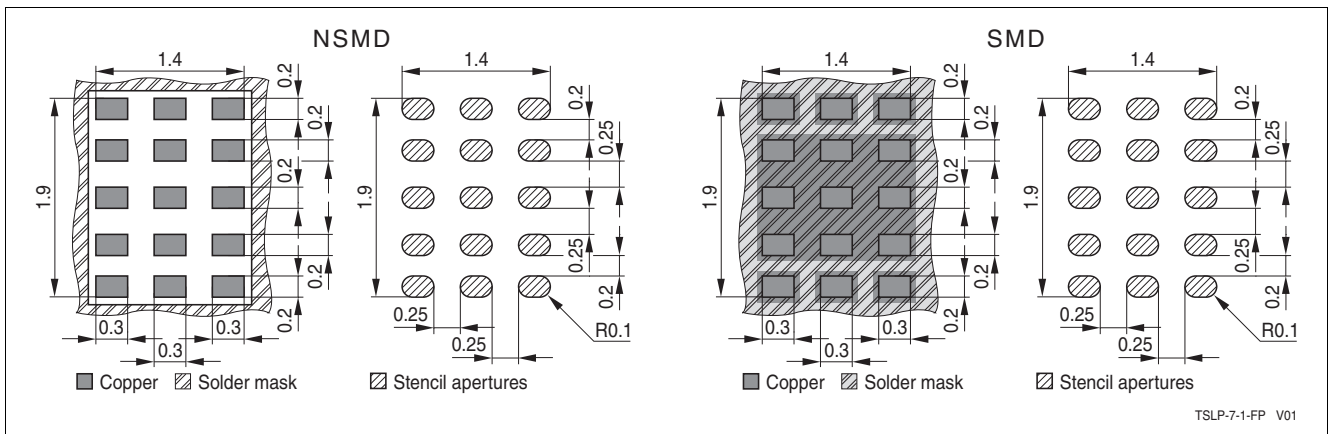


Figure 4 Footprint TSLP-7-1

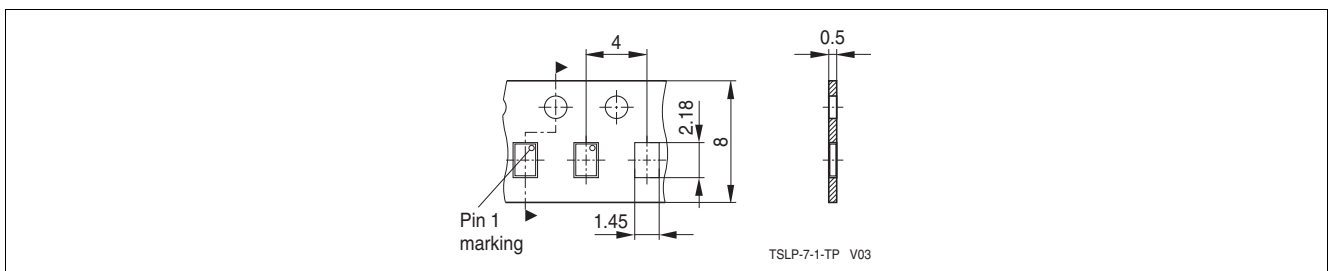


Figure 5 Tape & Reel Dimensions (Ø reel 180 mm, pieces/reel 7500)

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